

In the Abstract:

Please rewrite the abstract as follows:

~~The invention relates to a~~ A nonvolatile memory cell, memory cell arrangement, and method for production of a nonvolatile memory cell is disclosed. The nonvolatile memory cell comprises includes a vertical field-effect transistor (FET), with. The FET contains a nanoelement arranged as a channel region and an electrically insulating layer. The electrically insulating layer at least partially surrounding surrounds the nanoelement and acts as a charge storage layer and as a gate-insulating layer. The electrically insulating layer above is arranged such that electrical charge carriers may be selectively introduced into or removed from the electrically insulating layer above and the electrical conductivity characteristics of the nanoelement may be influenced by the electrical charge carriers introduced into the electrically insulating layer.